

**AMENDMENTS TO THE SPECIFICATION:**

Please add the following new paragraph immediately after the title appearing on page 1.

This application claims priority under 35 USC § 119 to European application No. 0 340 5223.3, filed April 2, 2003, and under 35 USC §371 to International Application No. PCT/CH2004/000204, filed April 1, 2004, the contents of which are incorporated herein by reference in their entirety.

Please amend the paragraph beginning on page 1, line 5 and ending on page 1, line 9

The invention described herein relates to the field of semiconductor devices.. It relates in particular to a manufacturing method for a power semiconductor module with reduced partial discharge behavior and a power semiconductor module with reduced partial discharge behavior ~~as described in the preamble of the independent claims.~~

Please delete the paragraph beginning on page 2, line 20, and ending on page 2, line 23.